

The 21<sup>st</sup> Korean Conference on Semiconductors  
**제21회 한국반도체학술대회**  
February 24–26, 2014 / Hanyang University, Seoul, Korea

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A. Interconnect & Package 분과

**[TC1-A] Atomic Layer Deposition and Silicides**

<b>Date</b>	Feb. 25, 2014 (Tue.)
<b>Place</b>	Room C / 제1공학관 401호 (# 401, Engineering Building I)

Session Chair: 이원준 교수(세종대학교),

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- TC1-A-1 09:30-09:45 Area-Selective Chemical Vapor Deposition of Co for Reduction of Cu Electromigration**  
저자: Jaehong Yoon<sup>1</sup>, Soohyeon Kim<sup>1</sup>, Han-Bo-Ram Lee<sup>2</sup>, Byeongchul Cho<sup>3</sup>, and Hyungjun Kim<sup>1</sup>  
소속: <sup>1</sup>School of Electrical and Electronic Engineering, Yonsei University, <sup>2</sup>Department of Materials Science and Engineering, Incheon National University, <sup>3</sup>Wonik IPS
- TC1-A-2 09:45-10:00 Silicidation of Ni prepared by Atomic Layer Deposition with NH<sub>3</sub> Gas Reactant**  
저자: Soohyeon Kim, Jaehong Yoon, Han-Bo-Ram Lee, and Hyungjun Kim  
소속: Department of Electrical and Electronics Engineering, Yonsei University, Department of Materials Science and Engineering, Incheon National University
- TC1-A-3 10:00-10:15 Highly Conformal Cu<sub>2</sub>O Thin Films by Atomic Layer Deposition using a New Non-Fluorinated Cu Precursor**  
저자: Hangil Kim<sup>1</sup>, Seung-Joon Lee<sup>1</sup>, Taehoon Cheon<sup>2</sup>, Sang-Kyung Choi<sup>3</sup>, and Soo-Hyun Kim<sup>1</sup>  
소속: <sup>1</sup>School of Materials Science and Engineering, Yeungnam University, <sup>2</sup>Senter for Core Research Facilities, Daegu Gyeongbuk Institute of Science & Technology, <sup>3</sup>Center for Research Facilities, Chungnam National University
- TC1-A-4 10:15-10:30 Growth of Ru Thin Film by Thermal Atomic Layer Deposition using a New Beta-Diketonate Ru Precursor and O<sub>2</sub> or NH<sub>3</sub> Molecules as a Seed Layer for Cu Electroplating**  
저자: Seung-Joon Lee<sup>1</sup>, Minyoung Lee<sup>1</sup>, Taehoon Cheon<sup>1,2</sup>, Soo-Hyun Kim<sup>1</sup>, Masayuki Saito<sup>3</sup>, Kazuharu Suzuki<sup>3</sup>, and Shunichi Nabeya<sup>3</sup>  
소속: <sup>1</sup>School of Materials Science and Engineering, Yeungnam University, <sup>2</sup>Center for Core Research Facilities, Deagu Gyeonbuk institute of Science & Technology, <sup>3</sup>TANAKA Kikinzoku Kogyo K.K
- TC1-A-5 10:30-10:45 Development of Yb Silicide with Low Schottky Barrier by Forming Epitaxial Layer**  
저자: Sekwon Na, Jun-gu Kang, Juyun Choi, Hyoungsub Kim, and Hoo-jeong Lee  
소속: School of Advanced Materials Science and Engineering, Sungkyunkwan University